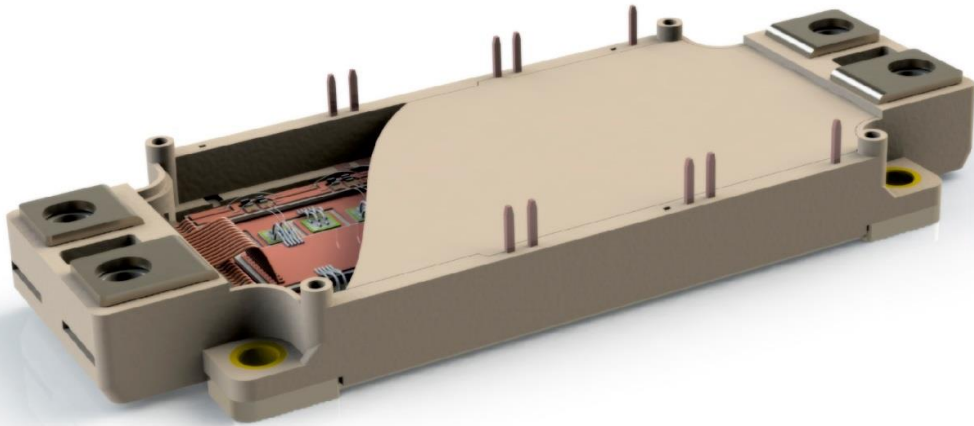




PROTON-ELECTROTEX
POWER SEMICONDUCTOR DEVICES

Full-SiC MODULE MCDA

1200V 500A low inductance H-Bridge /Phase-leg module in standard footprint



MODULE FEATURES:

- Full-SiC module with latest generation SiC MOSFET and SiC SBD
- Very low stray inductance (<8nH) in standard footprint
- Switching cell topology
- H-Bridge (250A) or Phase leg (500A)
- Low $R_{DS(on)}$ (<3.5 mOhm)
- Optimized gate-source circuit
- AlN substrate
- AlSiC baseplate
- Low die thermal coupling

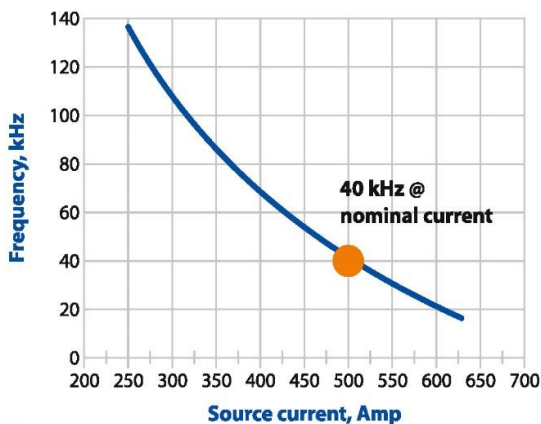
MODULE ADVANTAGES:

- Standard footprint
- Low conduction and ultra-low switching losses
- Fast and clean switching with minimum voltage overshoot and ringing
- Excellent die current sharing
- High thermal performance
- High thermal cycling performance

SYSTEM BENEFITS:

- High frequency operation
- Design flexibility and small size
- System cost reduction

OPERATING FREQUENCY VS CURRENT



SWITCHING CELL H-BRIDGE TOPOLOGY

